

High Intensity LED in \varnothing 5 mm Clear Package

Color	Type	Technology	Angle of Half Intensity $\pm\varphi$
Double hetero red	TLDR5800	GaAlAs on GaAs	4°

Description

This LED contains the double heterojunction (DH) GaAlAs on GaAs technology.

This deep red LED can be utilized over a wide range of drive current. It can be DC or pulse driven to achieve desired light output.

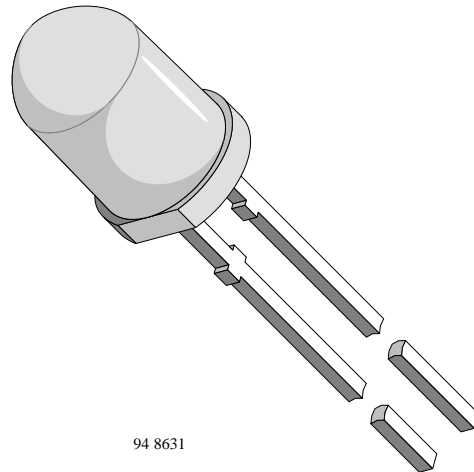
A clear 5 mm package is used to provide an extremely high light intensity of more than 2000 mcd at a very narrow viewing angle.

Features

- Exceptional brightness ($I_{V_{typ}} = 2500$ mcd at $I_F = 20$ mA)
- Very high intensity even at low drive currents
- Narrow viewing angle ($\varphi = \pm 4^\circ$)
- Low forward voltage
- 5 mm (T-1 $\frac{3}{4}$) clear package
- Deep red color
- Categorized for luminous intensity
- Outstanding material efficiency

Applications

Bright ambient lighting conditions
Battery powered equipment
Indoor and outdoor information displays
Portable equipment
Telecommunication indicators
General use



Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Double hetero red (TLDR5800)

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage			V_R	6	V
DC forward current			I_F	50	mA
Surge forward current	$t_p \leq 10 \mu\text{s}$		I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 65^{\circ}\text{C}$		P_V	100	mW
Junction temperature			T_j	100	$^{\circ}\text{C}$
Operating temperature range			T_{amb}	-20 to +100	$^{\circ}\text{C}$
Storage temperature range			T_{stg}	-55 to +100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5 \text{ s}$, 2 mm from body		T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient			R_{thJA}	350	K/W

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Double hetero red (TLDR5800)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	$I_F = 20 \text{ mA}$, $I_{V_{min}}/I_{V_{max}} \geq 0.5$		I_V	1000	2500		mcd
Dominant wavelength	$I_F = 20 \text{ mA}$		λ_d		648		nm
Peak wavelength	$I_F = 20 \text{ mA}$		λ_p		650		nm
Angle of half intensity	$I_F = 20 \text{ mA}$		ϕ		± 4		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		1.8	2.2	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1 \text{ MHz}$		C_j		50		pF

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

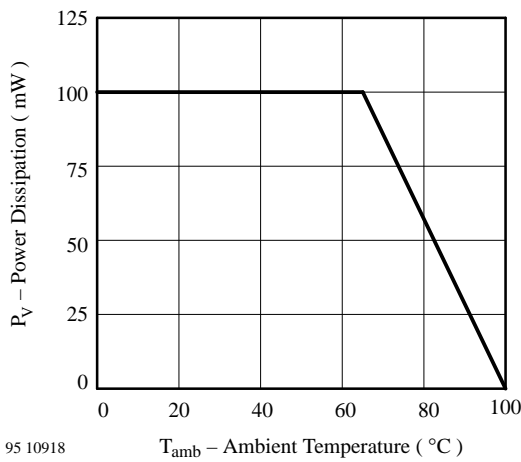


Figure 1. Power Dissipation vs. Ambient Temperature

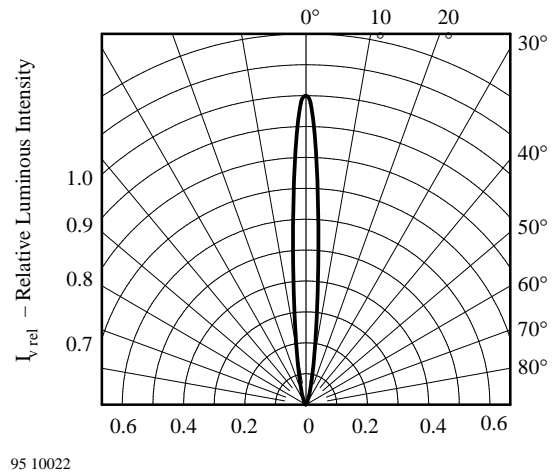


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

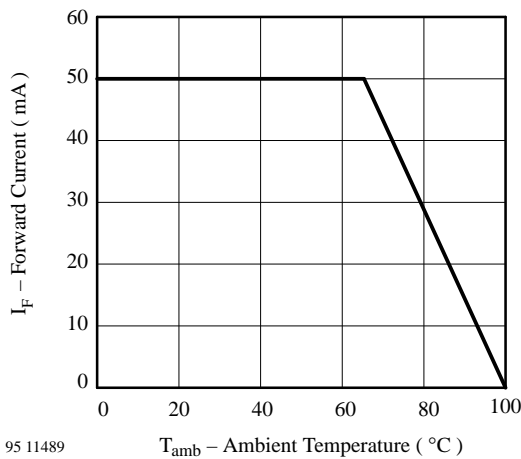


Figure 2. Forward Current vs. Ambient Temperature

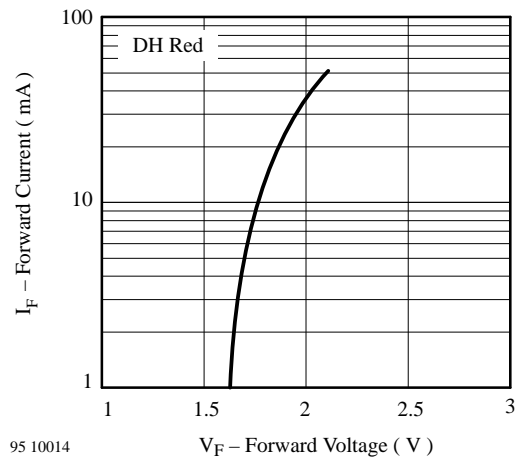


Figure 5. Forward Current vs. Forward Voltage

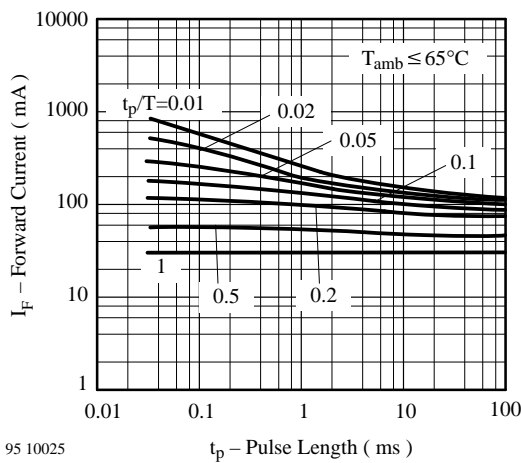


Figure 3. Forward Current vs. Pulse Length

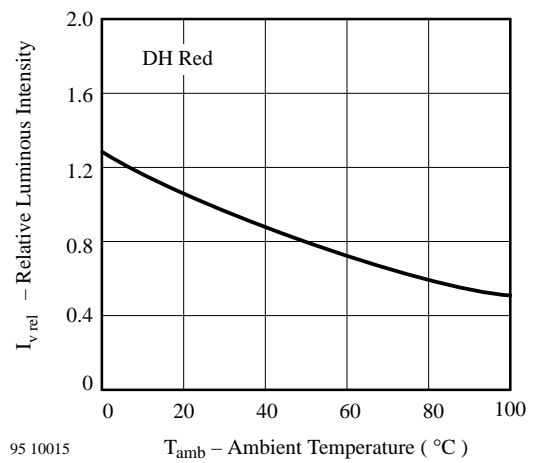


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature

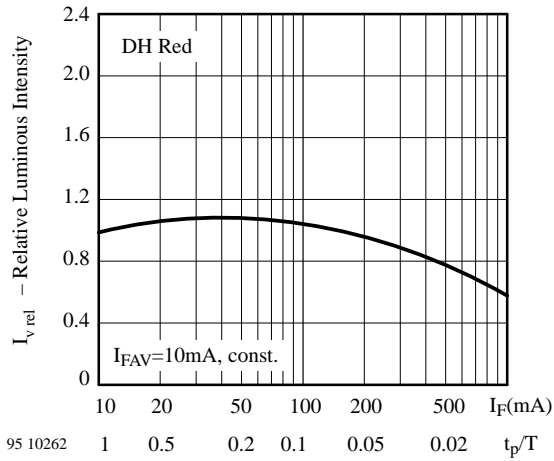


Figure 7. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

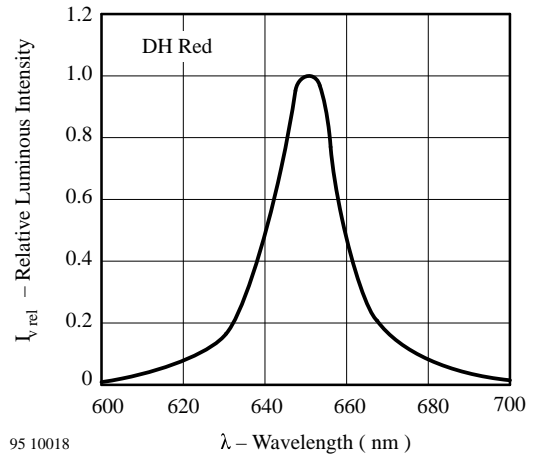


Figure 9. Relative Luminous Intensity vs. Wavelength

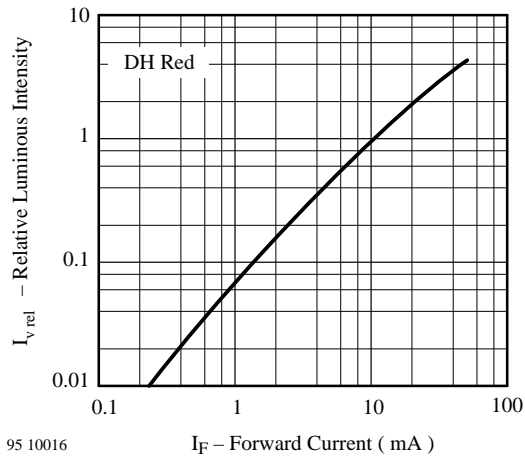
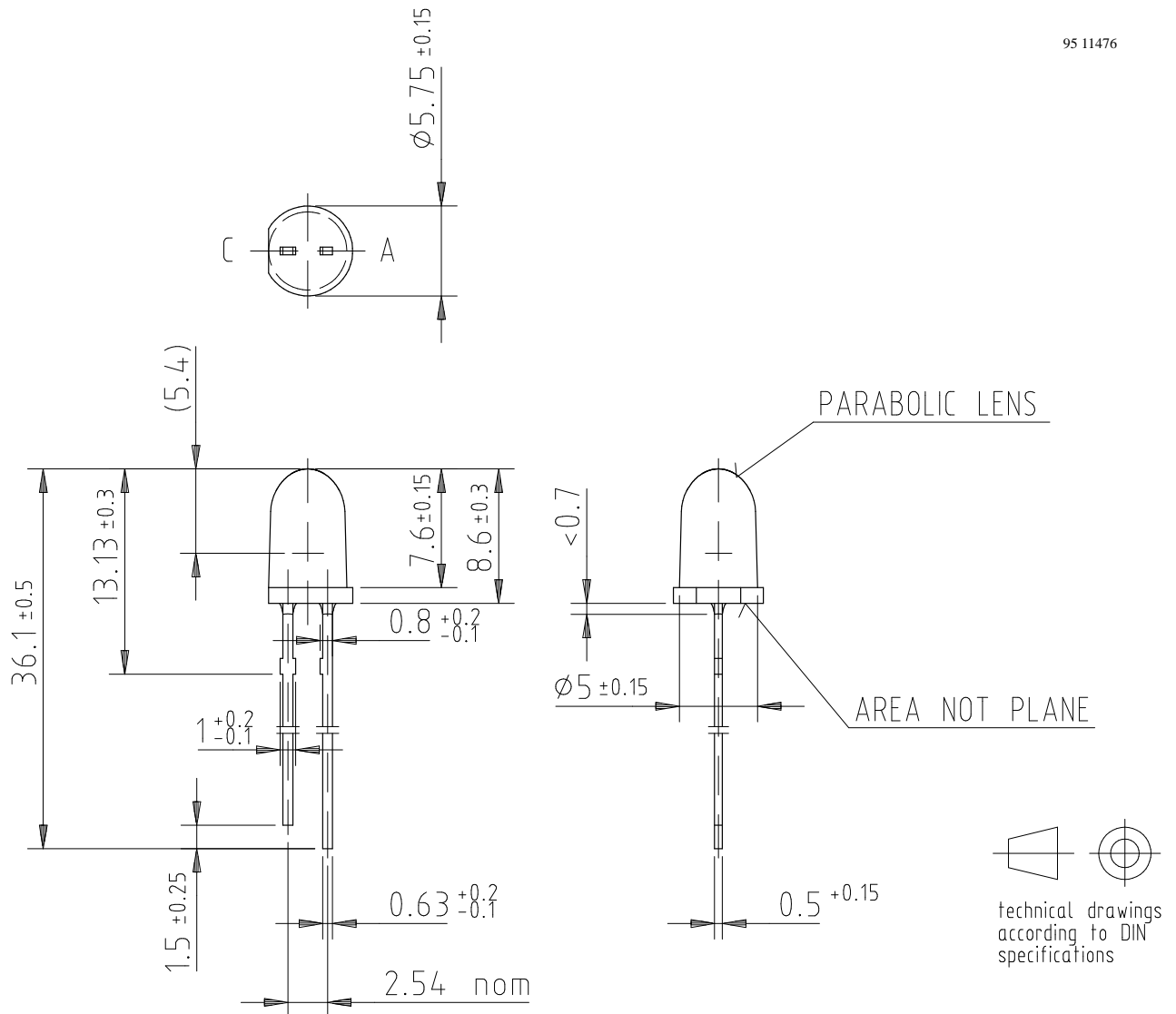


Figure 8. Relative Luminous Intensity vs. Forward Current

Dimensions in mm

95 11476



Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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